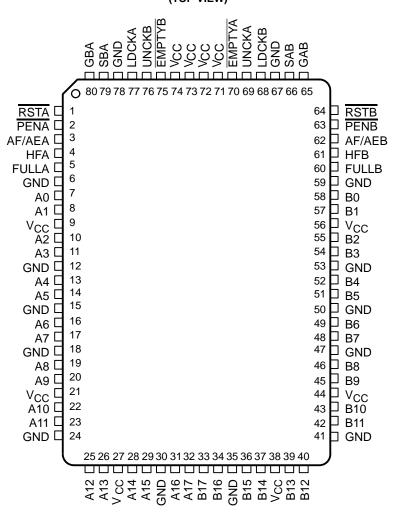
SCAS206B - AUGUST 1991 - REVISED SEPTEMBER 1995

- Member of the Texas Instruments Widebus ™ Family
- Independent Asynchronous Inputs and **Outputs**
- **Produced in Advanced BiCMOS Technology**
- Two Separate 512 × 18 FIFOs Buffering Data in Opposite Directions

- Programmable Almost-Full/Almost-Empty **Flags**
- Empty, Full, and Half-Full Flags
- Fast Access Times of 12 ns With a 50-pF Load and Simultaneous Switching Data **Outputs**
- Supports Clock Rates up to 67 MHz
- Available in 80-Pin Quad Flat (PH) and Space-Saving 80-Pin Thin Quad Flat (PN) **Packages**

PH PACKAGE (TOP VIEW)



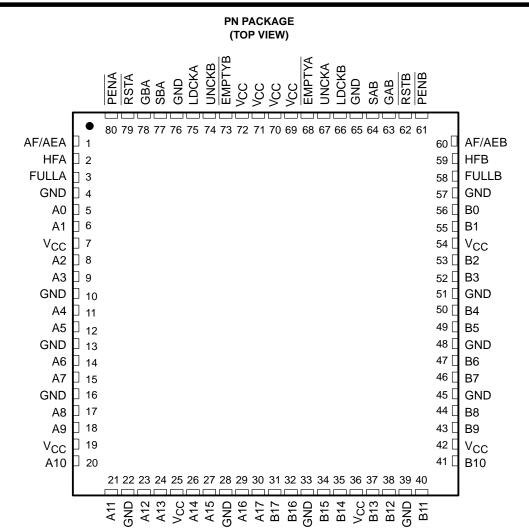


Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

Widebus is a trademark of Texas Instruments Incorporated



SCAS206B - AUGUST 1991 - REVISED SEPTEMBER 1995



description

A FIFO memory is a storage device that allows data to be written into and read from its array at independent data rates. The SN74ABT7820 is arranged as two 512 by 18-bit FIFOs for high speed and fast access times. It processes data at rates from 0 to 67 MHz with access times of 12 ns in a bit-parallel format.

The SN74ABT7820 consists of bus-transceiver circuits, two 512×18 FIFOs, and control circuitry arranged for multiplexed transmission of data directly from the data bus or from the internal FIFO memories. Enable inputs (GAB and GBA) control the transceiver functions. The SAB and SBA control inputs select whether real-time or stored data is transferred. The circuitry used for select control eliminates the typical decoding glitch that occurs in a multiplexer during the transition between stored and real-time data. Figure 1 illustrates the eight fundamental bus-management functions that can be performed with the SN74ABT7820.

The SN74ABT7820 is characterized for operation from 0°C to 70°C.



SCAS206B - AUGUST 1991 - REVISED SEPTEMBER 1995

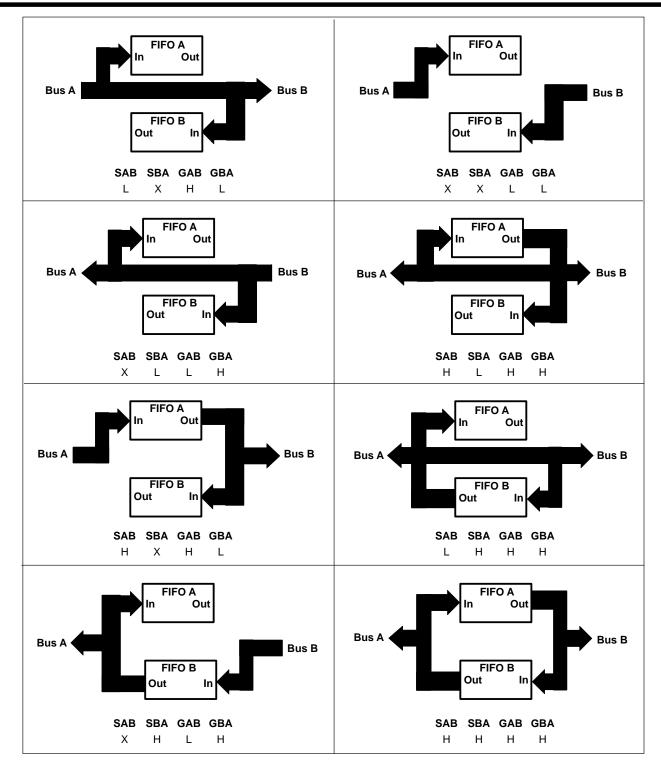


Figure 1. Bus-Management Functions



STROBED BIDIRECTIONAL FIRST-IN, FIRST-OUT MEMORY SCAS206B - AUGUST 1991 - REVISED SEPTEMBER 1995

SELECT-MODE CONTROL TABLE

CON	ΓROL	OPER	ATION
SBA	SAB	A BUS	B BUS
L	L	Real-time B to A bus	Real-time A to B bus
Н	L	FIFO B to A bus	Real-time A to B bus
L	Н	Real-time B to A bus	FIFO A to B bus
Н	Н	FIFO B to A bus	FIFO A to B bus

OUTPUT-ENABLE CONTROL TABLE

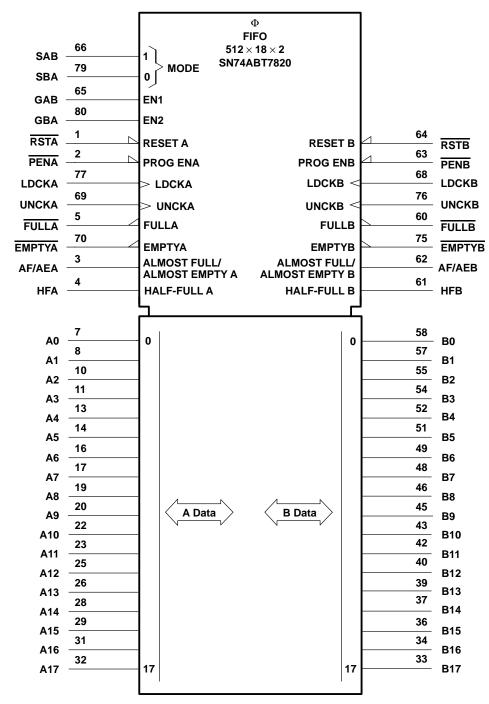
CON	ΓROL	OPERATION				
GBA	GAB	A BUS	B BUS			
L	L	Isolation/input to A bus	Isolation/input to B bus			
Н	L	A bus enabled	Isolation/input to B bus			
L	Н	Isolation/input to A bus	B bus enabled			
Н	Н	A bus enabled	B bus enabled			

Figure 1. Bus-Management Functions (Continued)



SCAS206B - AUGUST 1991 - REVISED SEPTEMBER 1995

logic symbol†

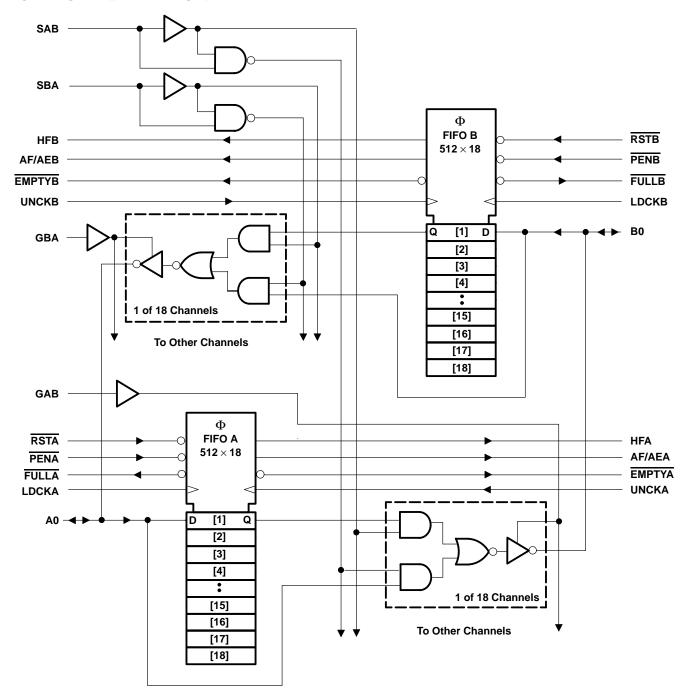


[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12. Pin numbers shown are for the PH package.



STROBED BIDIRECTIONAL FIRST-IN, FIRST-OUT MEMORY SCAS206B – AUGUST 1991 – REVISED SEPTEMBER 1995

logic diagram (positive logic)





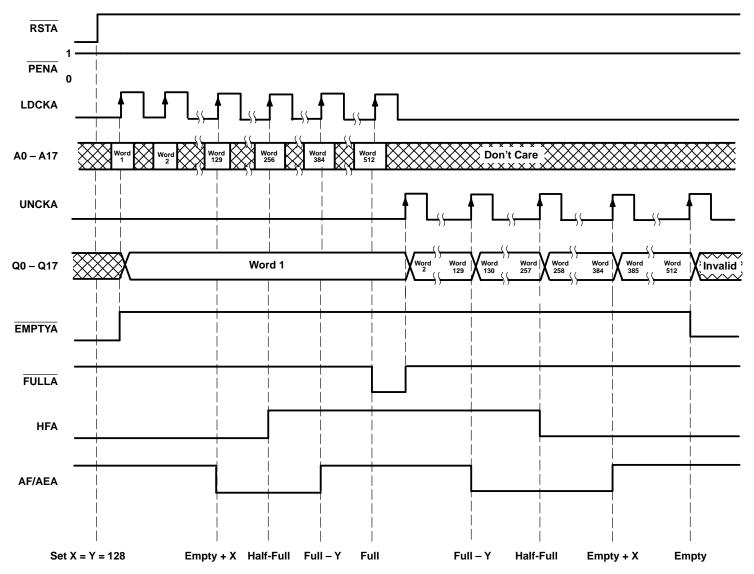
STROBED BIDIRECTIONAL FIRST-IN, FIRST-OUT MEMORY SCAS206B - AUGUST 1991 - REVISED SEPTEMBER 1995

Terminal Functions

TERMINAL	I/O	DESCRIPTION
A0-A17	I/O	Port-A data. The 18-bit bidirectional data port for side A.
AF/AEA	0	FIFO A almost-full/almost-empty flag. Depth-offset values can be programmed for AF/AEA or the default value of 128 can be used for both the almost-empty offset (X) and the almost-full offset (Y). AF/AEA is high when FIFO A contains X or less words or (512 – Y) or more words. AF/AEA is set high after FIFO A is reset.
AF/AEB	0	FIFO B almost-full/almost-empty flag. Depth-offset values can be programmed for AF/AEB or the default value of 128 can be used for both the almost-empty offset (X) and the almost-full offset (Y). AF/AEB is high when FIFO B contains X or less words or (512 – Y) or more words. AF/AEB is set high after FIFO B is reset.
B0-B17	I/O	Port-B data. The 18-bit bidirectional data port for side B.
EMPTYA	0	FIFO A empty flag. EMPTYA is low when FIFO A is empty and high when FIFO A is not empty. EMPTYA is set low after FIFO A is reset.
EMPTYB	0	FIFO B empty flag. EMPTYB is low when FIFO B is empty and high when FIFO B is not empty. EMPTYB is set low after FIFO B is reset.
FULLA	0	FIFO A full flag. FULLA is low when FIFO A is full and high when FIFO A is not full. FULLA is set high after FIFO A is reset.
FULLB	0	FIFO B full flag. FULLB is low when FIFO B is full and high when FIFO B is not full. FULLB is set high after FIFO B is reset.
GAB	I	Port-B output enable. B0-B17 outputs are active when GAB is high and in the high-impedance state when GAB is low.
GBA	I	Port-A output enable. A0 – A17 outputs are active when GBA is high and in the high-impedance state when GBA is low.
HFA	0	FIFO A half-full flag. HFA is high when FIFO A contains 256 or more words and is low when FIFO A contains 255 or less words. HFA is set low after FIFO A is reset.
HFB	0	FIFO B half-full flag. HFB is high when FIFO B contains 256 or more words and is low when FIFO B contains 255 or less words. HFB is set low after FIFO B is reset.
LDCKA	I	FIFO A load clock. Data is written into FIFO A on a low-to-high transition of LDCKA when FULLA is high. The first word written into an empty FIFO A is sent directly to the FIFO A data outputs.
LDCKB	I	FIFO B load clock. Data is written into FIFO B on a low-to-high transition of LDCKB when FULLB is high. The first word written into an empty FIFO B is sent directly to the FIFO B data outputs.
PENA	I	FIFO A program enable. After reset and before a word is written into FIFO A, the binary value on A0–A7 is latched as an AF/AEA offset value when PENA is low and LDCKA is high.
PENB	I	FIFO B program enable. After reset and before a word is written into FIFO B, the binary value on B0-B7 is latched as an AF/AEB offset value when PENB is low and LDCKB is high.
RSTA	I	FIFO A reset. A low level on RSTA resets FIFO A forcing EMPTYA low, HFA low, FULLA high, and AF/AEA high.
RSTB	ı	FIFO B reset. A low level on RSTB resets FIFO B forcing EMPTYB low, HFB low, FULLB high, and AF/AEB high.
SAB	I	Port-B read select. SAB selects the source of B0 – B17 read data. A low level selects real-time data from A0 – A17. A high level selects the FIFO A output.
SBA	I	Port-A read select. SBA selects the source of A0 – A17 read data. A low level selects real-time data from B0 – B17. A high level selects the FIFO B output.
UNCKA	I	FIFO A unload clock. Data is read from FIFO A on a low-to-high transition of UNCKA when EMPTYA is high.
UNCKB	I	FIFO B unload clock. Data is read from FIFO B on a low-to-high transition of UNCKB when EMPTYB is high.



timing diagram for FIFO A†



[†] SAB = GAB = H, GBA = L Operation of FIFO B is identical to that of FIFO A.



SCAS206B - AUGUST 1991 - REVISED SEPTEMBER 1995

offset values for AF/AE

The almost-full/almost-empty flag of each FIFO has two programmable limits: the almost-empty offset value (X) and the almost-full offset value (Y). The offsets of a flag can be programmed from the input of its FIFO after it is reset and before any data is written to its memory. An AF/AE flag is high when its FIFO contains X or less words or (512 – Y) or more words.

To program the offset values for AF/AEA, program enable (PENA) can be brought low after FIFO A is reset and only when LDCKA is low. On the following low-to-high transition of LDCKA, the binary value on A0–A7 is stored as the almost-empty offset value (X) and the almost-full offset value (Y). Holding PENA low for another low-to-high transition of LDCKA reprograms Y to the binary value on A0–A7 at the time of the second LDCKA low-to-high transition.

PENA can be brought back high only when LDCKA is low during the first two LDCKA cycles. PENA can be brought high at any time after the second LDCKA pulse returns low. A maximum value of 255 can be programmed for either X or Y (see Figure 2). To use the default values of X = Y = 128 for AF/AEA, PENA must be tied high. No data is stored in the FIFO when its AF/AE offsets are programmed. The AF/AEB flag is programmed in the same manner. PENB enables LDCKB to program the AF/AEB offset values taken from B0-B7.

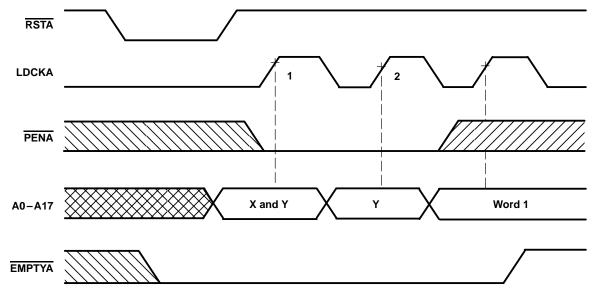


Figure 2. Programming X and Y Separately for AF/AEA



SCAS206B - AUGUST 1991 - REVISED SEPTEMBER 1995

absolute maximum ratings over operating free-air temperature (unless otherwise noted)

Supply voltage range, V_{CC} –0.5 V to 7 V Input voltage range, V_I (see Note 1) –0.5 V to V_{CC} + 0.5 V Voltage range applied to any output in the high state or power-off state, V_O −0.5 V to 5.5 V Storage temperature range, T_{stq} –65°C to 150°C

recommended operating conditions

		MIN	NOM	MAX	UNIT
VCC	Supply voltage	4.5	4.5	5.5	V
VIH	High-level input voltage	2			V
V _{IL}	Low-level input voltage			0.8	V
٧ _I	Input voltage	0		VCC	V
I _{ОН}	High-level output current			-12	mA
l _{OL}	Low-level output current			24	mA
$\Delta t/\Delta v$	Input transition rise or fall rate			5	ns/V
TA	Operating free-air temperature	0		70	°C

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PA	RAMETER		TEST		MIN	TYP‡	MAX	UNIT	
VIK		$V_{CC} = 4.5 \text{ V},$			- 1.2	V			
		$V_{CC} = 4.5 \text{ V},$	$I_{OH} = -3 \text{ mA}$			2.5			
Vон		$V_{CC} = 5 V$,	$I_{OH} = -3 \text{ mA}$			3			V
		$V_{CC} = 4.5 \text{ V},$	I _{OH} = – 12 m/	4		2			
V_{OL} $V_{CC} = 4.5 \text{ V}, \qquad I_{OL} = 24 \text{ mA}$							0.55	V	
Ц	$V_{CC} = 5.5 \text{ V}, \qquad V_{I} = V_{CC} \text{ or GND}$						±5	μΑ	
I _{OZH} §		$V_{CC} = 5.5 \text{ V}, \qquad V_{O} = 2.7 \text{ V}$						50	μΑ
I _{OZL} §		$V_{CC} = 5.5 \text{ V},$	$V_0 = 0.5 V$					- 50	μΑ
IO¶		$V_{CC} = 5.5 \text{ V},$	V _O = 2.5 V			- 40	- 100	- 180	mA
					Outputs high			15	
^I CC		$V_{CC} = 5.5 V$,	$I_{O} = 0$,	$V_I = V_{CC}$ or GND	Outputs low			95	mA
					Outputs disabled			15	
Ci	Control inputs	V _I = 2.5 V or 0.5 V					6		pF
Co	Flags $V_0 = 2.5 \text{ V or } 0.5 \text{ V}$						4		pF
C _{io}	A or B ports	$V_0 = 2.5 \text{ V or } 0.$	5 V				8		pF

[‡] All typical values are at V_{CC} = 5 V, T_A = 25°C.



[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

[§] The parameters IOZH and IOZL include the input leakage current.

 $[\]P$ Not more than one output should be tested at a time, and the duration of the test should not exceed one second.

STROBED BIDIRECTIONAL FIRST-IN, FIRST-OUT MEMORY SCAS206B - AUGUST 1991 - REVISED SEPTEMBER 1995

timing requirements over recommended operating free-air temperature range (unless otherwise noted)

			′ABT78	320-15	′ABT78	320-20	′ABT78	320-25	′ABT7820-30		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	UNII
f _{clock}	Clock frequenc	су	67		50		40		33		MHz
		LDCKA, LDCKB high	4		6		9		11		
		LDCKA, LDCKB low	4		6		9		11		
t _W	Pulse duration	UNCKA, UNCKB high	4		6		9		11		ns
	duration	UNCKA, UNCKB low	4		6		9		11		
		RSTA, RSTB low	6		8		10		12		
		A0-A17 before LDCKA↑ and B0-B17 before LDCKB↑	3		4		4		4		
t _{su}	Setup time	PENA before LDCKA↑ and PENB before LDCKB↑	5		5		5		5		ns
		LDCKA inactive before RSTA high and LDCKB inactive before RSTB high	3		3		4		4		
		A0−A17 after LDCKA↑ and B0−B17 after LDCKB↑	0		0		0		0		
t _h	Hold time	PENA after LDCKA low and PENB after LDCKB low	2		2		2		2		ns
		LDCKA inactive after RSTA high and LDCKB inactive after RSTB high	3		3		4		4		

STROBED BIDIRECTIONAL FIRST-IN, FIRST-OUT MEMORY SCAS206B – AUGUST 1991 – REVISED SEPTEMBER 1995

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 5)

PARAMETER	FROM TO		TO 'ACT7820-15 'ACT7820-1		320-20	'ACT78	320-25	'ACT78	320-30	UNIT		
PARAMETER	(INPUT)	(OUTPUT)	MIN	TYP†	MAX	MIN	MAX	MIN	MAX	MIN	MAX	UNII
f _{max}	LDCK, UNCK				67		50		40		33.3	MHz
t _{pd}	LDCKA↑, LDCKB↑	B/A	4		14	4	15	4	18	4	20	ns
·ρu	UNCKA↑, UNCKB↑		4	9	12	4	13.5	4	15	4	17	
t _{pd} ‡	UNCKA↑, UNCKB↑	B/A		8								ns
tPLH	LDCKA↑, LDCKB↑	EMPTYA,	4		14	4	15	4	17	4	19	ns
^t PHL	UNCKA↑, UNCKB↑	EMPTYB	4		13	4	14	4	16	4	18	115
^t PHL	RSTA low, RSTB low	EMPTYA, EMPTYB	6		16	6	16	6	18	6	20	ns
^t PHL	LDCKA↑, LDCKB↑	FULLA, FULLB	6		13	6	14	6	16	6	18	ns
t	UNCKA↑, UNCKB↑	FULLA,	6		15	6	15	6	17	6	19	ns
^t PLH	RSTA low, RSTB low	FULLB	8		20	8	20	8	22	8	22	115
	LDCKA↑, LDCKB↑	AF/AEA,	8		16	8	17	8	18	8	20	ns
^t pd	UNCKA↑, UNCKB↑	AF/AEB	8		16	8	17	8	18	8	20	115
^t PLH	RSTA low, RSTB low	AF/AEA, AF/AEB	2		12	2	14	2	16	2	18	ns
^t PLH	LDCKA↑, LDCKB↑	HFA, HFB	8		15	8	15	8	17	8	19	ns
	UNCKA, UNCKB		8		15	8	15	8	17	8	19	
^t PHL	RSTA low, RSTB low	HFA, HFB	2		12	2	14	2	16	2	18	ns
to d	SAB/SBA§	B/A	2		10	2	11	2	12	2	14	ns
t _{pd}	A/B	DIΛ	2		9	2	10	2	11	2	13	ns
t _{en}	GBA/GAB	A/B	2		6.5	2	8	2	10	2	12	ns
^t dis	GBA/GAB	A/B	2		11	2	12	2	13	2	14	ns

[†] All typical values are at 5 V, $T_A = 25$ °C.



[‡] This parameter is measured with a 30-pF load (see Figure 3).

[§] These parameters are measured with the internal output state of the storage register opposite to that of the bus input.

TYPICAL CHARACTERISTICS

PROPAGATION DELAY TIME

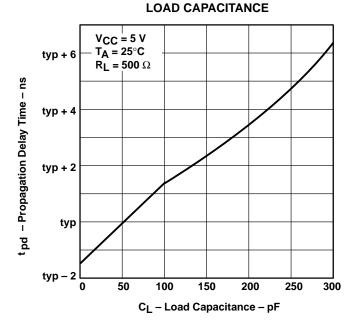


Figure 3

SUPPLY CURRENT vs

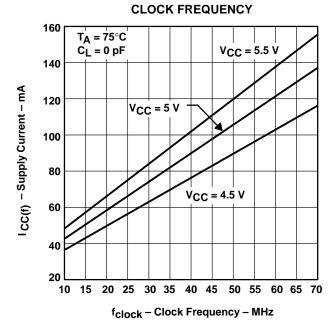


Figure 4

TYPICAL CHARACTERISTICS

calculating power dissipation

With $I_{CC(f)}$ taken from Figure 4, the maximum power dissipation (P_T) based on all outputs changing states on each read can be calculated by:

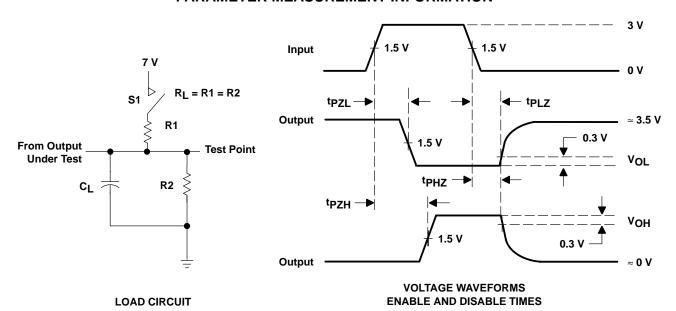
$$P_{T} = V_{CC} \times I_{CC(f)} + \Sigma(C_{L} \times V_{CC}^{2} \times f_{o})$$

where:

 $I_{CC(f)}$ = maximum I_{CC} per clock frequency

C_L = output capacitive load f_o = data output frequency

PARAMETER MEASUREMENT INFORMATION



PARAM	/IETER	R1, R2	CL†	S1
	^t PZH	500 Ω	50 pF	Open
ten	tpzL	300 12	50 pr	Closed
.	^t PHZ	500 Ω	50 pF	Open
^t dis	tPLZ	300 22	50 pr	Closed
^t pd		500 Ω	50 pF	Open

[†] Includes probe and test-fixture capacitance

Figure 5. Load Circuit and Voltage Waveforms



IMPORTANT NOTICE

Texas Instruments (TI) reserves the right to make changes to its products or to discontinue any semiconductor product or service without notice, and advises its customers to obtain the latest version of relevant information to verify, before placing orders, that the information being relied on is current.

TI warrants performance of its semiconductor products and related software to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

Certain applications using semiconductor products may involve potential risks of death, personal injury, or severe property or environmental damage ("Critical Applications").

TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, INTENDED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT APPLICATIONS, DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS.

Inclusion of TI products in such applications is understood to be fully at the risk of the customer. Use of TI products in such applications requires the written approval of an appropriate TI officer. Questions concerning potential risk applications should be directed to TI through a local SC sales office.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards should be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance, customer product design, software performance, or infringement of patents or services described herein. Nor does TI warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used.

Copyright © 1996, Texas Instruments Incorporated